

Midium Power Transistors (50V / 4A) 2SCR543D

Structure

NPN Silicon epitaxial planar transistor

Features

1) Low saturation voltage

 $V_{CE (sat)} = 0.35V (Max.) (I_C / I_B = 2A / 100mA)$

2) High speed switching

Applications

Driver

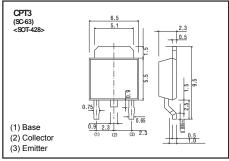
• Packaging specifications

	Package	CPT3
Туре	Code	TL
	Basic ordering unit (pieces)	2500

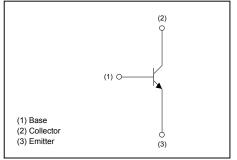
•Absolute maximum ratings (Ta=25°C)

Para	imeter	Symbol	Limits	Unit	
Collector-base voltage		V _{CBO}	50	V	
Collector-emitter voltage		V _{CEO}	50	V	
Emitter-base voltage	ge	V_{EBO}	6	V	
Collector current	DC	Ι _c	4	А	
	Pulsed	Ι _{CP} *1	8	А	
Power dissipation	dissination P _D *2 1 W		W		
		P _D *3	10	W	
Junction temperatu	lre	Tj	150	°C	
Range of storage temperature		T _{stg}	-55 to 150	°C	

• Dimensions (Unit : mm)



• Inner circuit (Unit : mm)



*1 Pw=10ms, Single Pulse

*2 Mounted on a substrate

*3 T_c=25°C

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	50	-	-	V	I _C = 1mA
Collector-base breakdown voltage	BV_{CBO}	50	-	-	V	Ι _C = 100μΑ
Emitter-base breakdown voltage	BV_{EBO}	6	-	-	V	Ι _Ε = 100μΑ
Collector cut-off current	I _{CBO}	-	-	1	μA	V _{CB} = 50V
Emitter cut-off current	I _{EBO}	-	-	1	μA	V _{EB} = 4V
Collector-emitter staturation voltage	V _{CE(sat)} [*] 1	-	130	350	mV	I _C = 2A, I _B = 100mA
DC current gain	h _{FE}	180	-	450	-	V _{CE} = 3V, I _C = 100mA
Transition frequency	f_{T}^{*1}	-	300	-	MHz	V _{CE} = 10V I _E =-500mA, f=100MHz
Collector output capacitance	C _{ob}	-	20	-	pF	V _{CB} = 10V, I _E =0A f=1MHz
Turn-on time	t _{on} * ₂	-	50	-	ns	$1 - 20 + - 200m^{4}$
Storage time	t _{stg} * ₂	-	450	-	ns	I _C = 2A, I _{B1} = 200mA, I _{B2} =-200mA, V _{CC} <u>∼</u> 10V
Fall time	t _f *2	-	85	-	ns	B2 2000 , CC 100

*1 Pulsed

*2 See switching time test circuit

•Electrical characteristic curves (Ta=25°C)

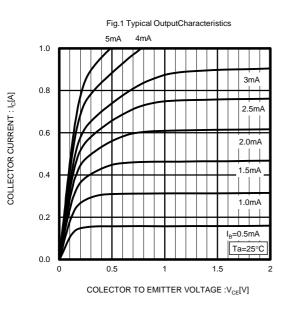


Fig3. DC Current Gain vs. Collector Current (II)

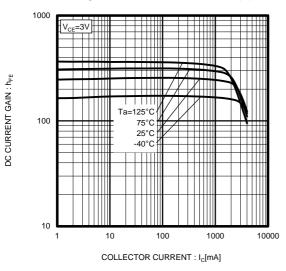


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II)

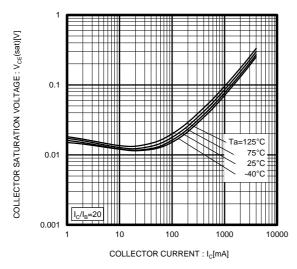


Fig.2 DC Current Gain vs. Collector Current (I)

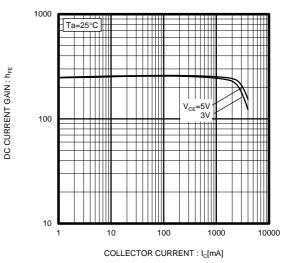
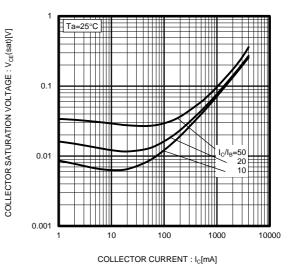
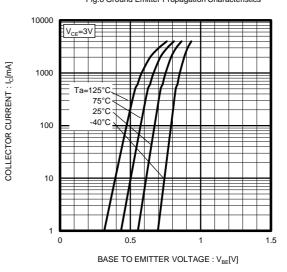
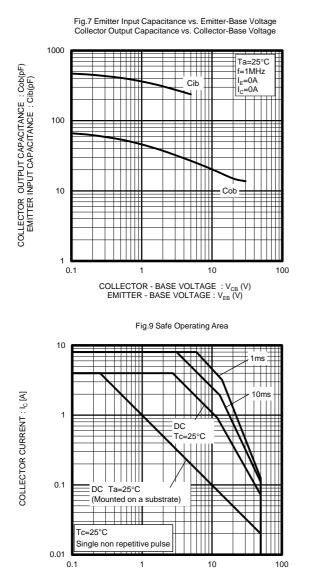


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)



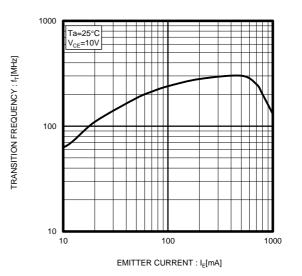




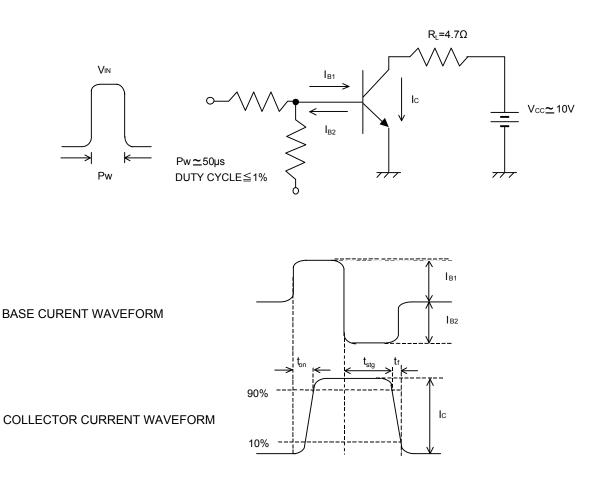


COLLECTOR TO EMITTER VOLTAGE : $V_{CE}[V]$

Fig.8 Gain Bandwidth Product vs. Emitter Current



• Switching time test circuit



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